

The Nano Revolution and Its Effects on Micro/Nano Systems Education

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This Conference

“Educating Tomorrow's
Microsystems Designers”



This Talk

“Educating Tomorrow’s ~~Micro~~systems Designers” *Nano*”



In More Detail

- Silicon Rules Today, But
- The “End of the Road” is in sight
- With “Nanotechnologies” in daily headlines
 - Potential for another 1,000X Moore’s Law
- And: Our Students will live through the transition

How do we prepare them ... Today!



Today's Discussion Topics

- **The National Nanotechnology Initiative**
- **A Walk Through Nano Land**
- **Lessons Best Not Forgotten**
- **Moving Towards a New Curriculum**
- **Concluding Thoughts**



Acknowledgements & References

- **NSF-Sponsored “Molecular Architecture Workshop (MAW)” @ Notre Dame in Nov. 2001**
– (Names in subtitles = MAW participants)
- **“Teaching students computer architecture for new, nanotechnologies,” M. Niemier & P. Kogge, ISCA Workshop on Computer Architecture Education, May 26, 2002**
- **Multiple sponsors: NSF, SRC, JPL, ...**
- **<http://nano.gov>**
- **Special thanks to Lynn Conway & Mary Jane Irwin**



Nano: Science, Engineering, & Technology

“Ability to work at *molecular* level,
atom by atom,
to *create large structures*
with fundamentally new
properties and *functions*”

M. Roco, NSF



The National Nanotechnology Initiative (NNI)



NNI: A Brief History

- **1996: Interagency discussions on nano**
- **1998: Interagency Working Group on Nanotechnology established**
- **1999: “Nanostructure Science & Technology: A World Wide Study”**
- **2000: NNI becomes federal initiative**
 - 2001 funding authorized @ \$464M
- **2001: NSET (Nanoscale Science, Engr, & Technology) subcommittee to provide policy leadership**
- **May 7, 2003: H.R. 766 authorizes \$2.36B over 3 years**

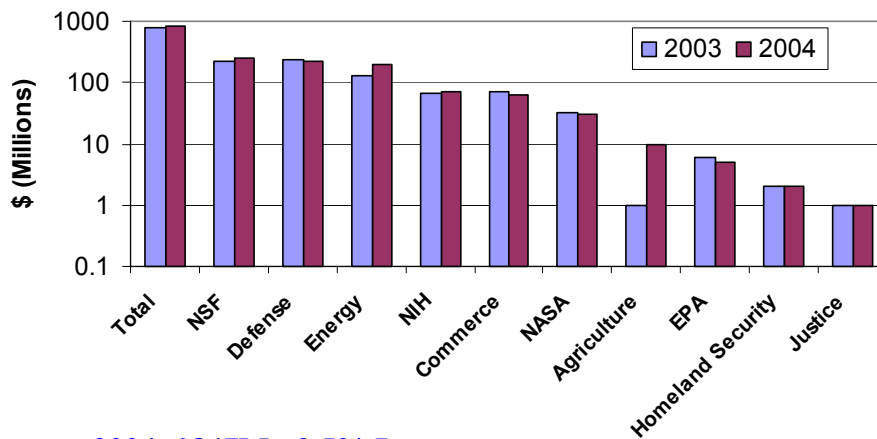
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The NNI Today



2004: \$847M - 9.5% Increase

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Where is the \$ Going (2002 NSF NIRT)

- Biosystems: 3 @ \$5M
- Structures & Phenomena: 18 @ \$24
- Theory, Modeling, & Simulation: 2 @ \$2.3M
- Manufacturing: 16 @ \$17.45M
- • Device & Systems Architecture: 12 @ \$16.6M
– Only 3 above the device level (~6%)



Where is the \$ Going (2002 NSF NER)

- Biosystems: 7 @ \$585K
- Structures & Phenomena: 21 @ \$1.99M
- Theory, Modeling, & Simulation: 6 @ \$564K
- Nanoscale in Environment: 6 @ \$571K
- Manufacturing: 15 @ \$1.39M
- Societal Implications: 2 @ \$280K
- • Device & Systems Architecture: 31 @ \$2.69M
– only 8 above the device level (~25%)



Some Key Planned NNI Outcomes

(from “Small Wonders, Endless Frontiers” Nat. Academy Press)

- **2005:**
 - 50% of research institutions have nano scale lab access
 - ➔ – Nano education in 25% of research institutions
 - Catalyse new markets depending on 3D nanostructures
 - 3D modeling for practical system & architecture design
- **2006:**
 - Demo terabit nano electronic memory chip
 - Use nano for contaminant monitoring
 - Nanoscale manufacturing for 3 new technologies
 - 10 R&D Centers support facilities for nanoscale testing & manufacturing



Post 2006

- Incorporate biological molecules into electronic devices
- Blueprints for nanomachines & synthetic molecular processors
- Incorporate photovoltaic proteins into nanosystems
- Incorporate “insect hearing organs” into nanosystems



Bottom Line Goal

- Create new industry
- Based on molecular scale devices
- That produces “large structures”
- With new “functions”
- *Within the college career of this year’s freshman class*



List of Nano Courses

(from <http://www.nsf.gov/home/crssprgm/nano/courses.htm>)

- Advanced Quantum Devices, University of Notre Dame
- Nano-course, Cornell Nanofabrication Facility
- New Technologies, University of Wisconsin, Madison
- Nanostructured Materials, Rensselaer Polytechnic Institute
- Colloid Chemical Approach to Construction of Nanoparticles and Nanostructured Materials, Clarkson University
- Nanoparticles Processes, Yale University
- Nanorobotics, South California University
- Nanotechnology, Virginia Commonwealth University
- Chemistry and Physics of Nanomaterials, University of Washington
- Scanning Probes and Nanostructure Characterization, Clemson
- Nano-scale Physics, Clemson University
- Capstone Course on Nanotechnology, Penn State Nanofab Facility
- Nanomanufacturing Processes, U. of Arkansas Oklahoma & Nebraska
- Nanoscale Science and Engineering, Purdue University
- Visual Quantum Mechanics, Kansas State University
- Mathematics in Nanoscale Science and Engineering, UCLA
- Nanotechnology: What's So Big About the Science of the Very Small, Rice



A Walk Through Nano Land (with a Stop at QCA)



Technology paradigms 101

- Past 7 decades, Zeus's paradigm, current switches dominate:



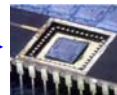
Electromechanical relay



Vacuum tubes



Solid-state transistors



CMOS IC

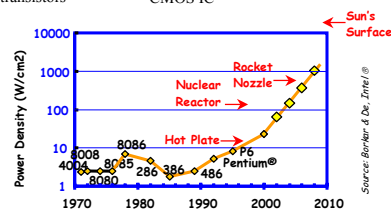
- But problems lurk...

Technical:

Quantum effects, e^- tunneling, power dissipation, slow wires, dopant concentrations, lithography resolutions, chip I/O, testing

Economical:

In 2010 a fabrication plant may cost \$200 billion!



Source: Barker & De Jure, ©



The "Silicon" Limits

- **Silicon 2016:**
 - 22 nm gate lengths,
 - 28 GHz clocks,
 - 310 sq.mm die
- **Roadblocks:**
 - Smaller devices won't work
 - *Significant changes in key design ratios*

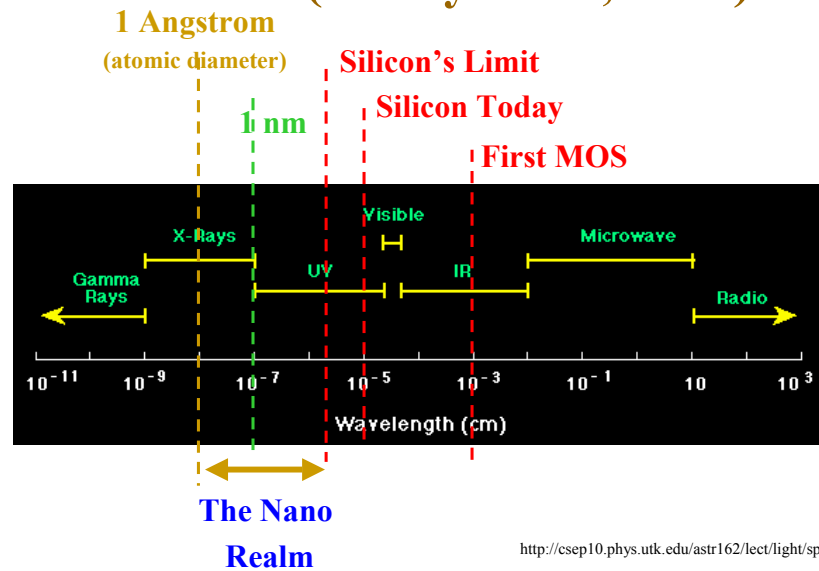
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There's Plenty of Room at the Bottom (R. Feynman, 1959)



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Computational Paradigms at the Nano Scale

- **Classical digital logic**
- **Neural Net**
- **Chemical-based**
- **DNA-based**
- **Quantum**



Working at Nano Dimensions

(Weiss)

- **Circuit limits: mean free path & coherence length of electron**
 - Ultimate computing device ~ trapping single electron in quantum dot
- **Growing capability to manipulate**
 - Properties of single molecules
 - Placement into monolayer films
 - With sharp boundaries
- **Molecular alignment & conductance states heavily influenced by neighboring molecules**
- **May provide basis for self-assembly**



Design Challenges in Moving to Molecular Realm

(Edwards, SRC)

What is needed to “commercialize”

- **Reliability:** what are new failure mechanisms
- “Software Reconfigurability” in the field
- **Controlling design time** as complexity grows
- **Speed:** maintaining Moore’s Law
- **Mixed Signal:** needed for “Systems on a Chip”
- **Test:** coverage, procedures, fixtures
- **Cost:** development, unit costs, components of cost

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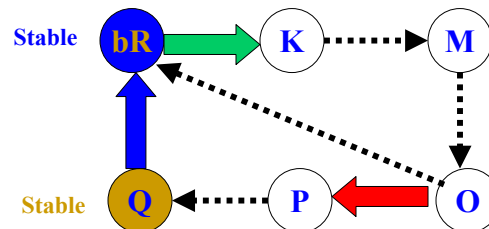
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Protein Computing

States of the bacteriorhodopsin molecules as a function of light:

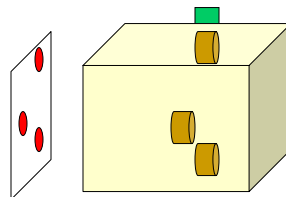


To Write:

- Shine green into slice
- Shine red to desired bits

To Read

- Shine green into slice
- Shine low red thru all
- Look at red output



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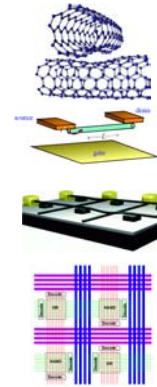
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Nano Tubes & Nano Wires

(Fuhrer, Goldstein, Dehon)

- Nanotube: nm wide metallic or semiconducting tube
- Producing numbers in lab
- Applications: interconnect, single electron FETs, micromechanical switches, levers, relays ...
- Most promising structures: arrays, crossbars, FPGAs, fabrics
- “Compile to space, not time”
- Challenges:
 - Alignment
 - Defect recovery/repair, fault tolerance
 - Micro-nano interfacing
 - Gain/signal restoration
 - Customization



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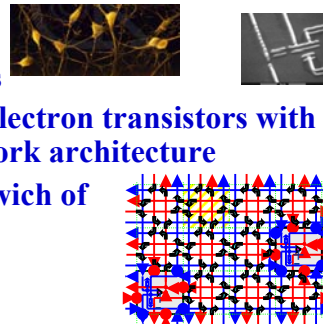
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“Network”-Driven Technology Developments

(Likarev, Porod, Chong)

- “Neural Net” as a natural fault-tolerant robust system architecture
- Silicon neural nets too small
 - Brain = 10^{10} cells with 10^{14} synapses
- Enabling nanotechnology: single electron transistors with randomized analog crossbar network architecture
- Growth to system: “Silicon” sandwich of
 - CMOS interconnect logic
 - SET processing elements
 - “Sensors”
- Similar: “sensor nets” merged into “environment”
 - Programming small nodes for aggregate behavior



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Quantum-dot Cellular Automata (a Notre Dame nano technology)

A cell with 4 dots, 2 extra electrons, tunneling between dots



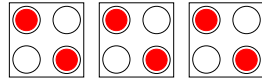
Represent binary information by charge configuration



Polarization $P = -1$
Bit value "0"

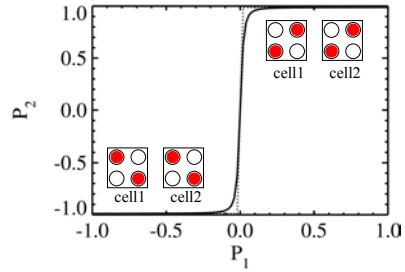


Polarization $P = +1$
Bit value "1"



Neighboring cells tend to align.
Coulombic coupling

Cell-cell response function



Bistable, nonlinear cell-cell response

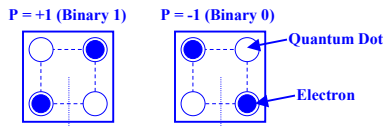
Restoration of signal levels

Robustness against disorder



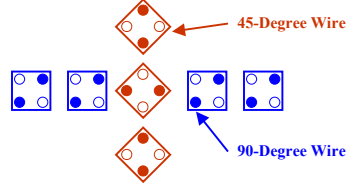
The Basics

The Device

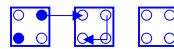


Proposed experiment – 42 nm
Future molecular – 4.2 nm
(and room temperature)

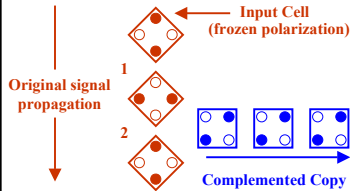
Wire Cross in the Plane



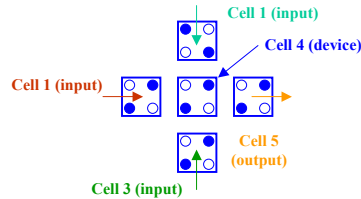
A QCA Wire



A 45-degree Wire

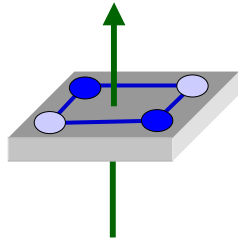


Majority Gate

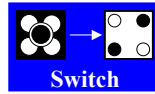




The QCA "Clock"

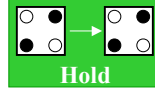


"Clock = E field that controls tunneling between dots"



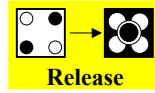
Switch

- Cells begin unpolarized
- Barriers raised, cells "latched"



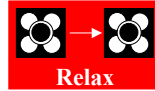
Hold

- Barriers are held high
- Used as input to next zone



Release

- Barriers are lowered
- Cells relax to unpolarized state



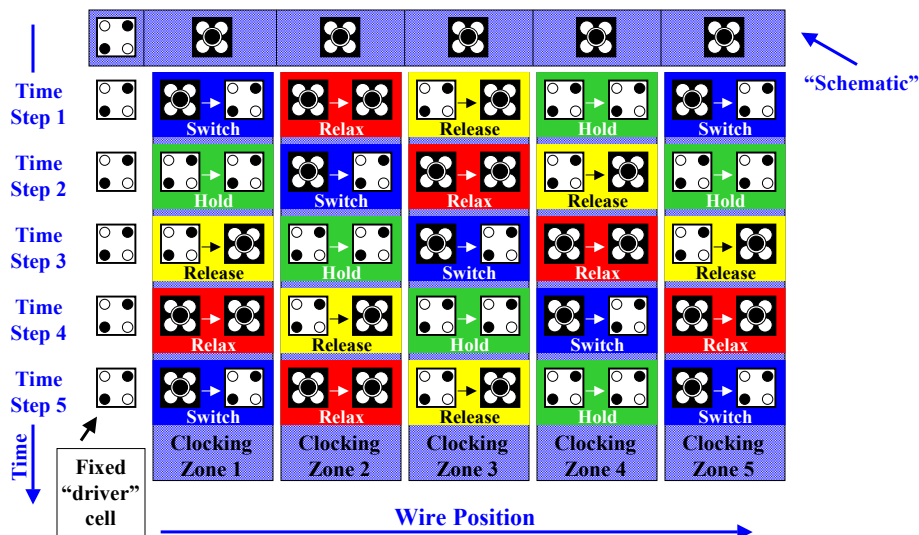
Relax

- Cell barriers remain lowered
- Unpolarized, neutral state stays

The QCA Clock "Phases"



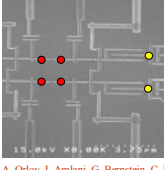
A clocking example





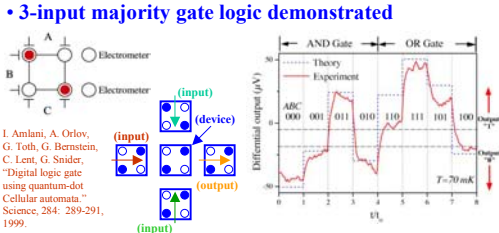
Experimental QCA

- Early and current work – metal dots
- 70 mK
- Metal dot “ideas” transfer to/across different QCA implementations



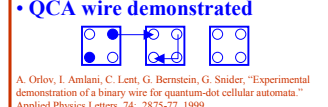
A. Orlov, I. Amlani, G. Bernstein, C. Lent, G. Snider, "Realization of a functional cell for quantum-dot cellular automata." *Science*, 277:928-930, 1997.

- 3-input majority gate logic demonstrated



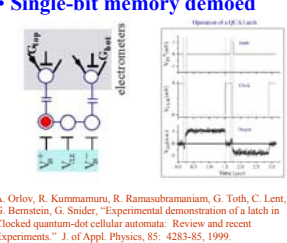
I. Amlani, A. Orlov, G. Toth, G. Bernstein, C. Lent, G. Snider, "Digital logic gate using quantum-dot Cellular automata." *Science*, 284: 289-291, 1999.

- QCA wire demonstrated



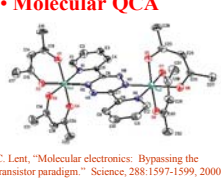
A. Orlov, I. Amlani, C. Lent, G. Bernstein, G. Snider, "Experimental demonstration of a binary wire for quantum-dot cellular automata." *Applied Physics Letters*, 74: 2875-77, 1999.

- Single-bit memory demoed



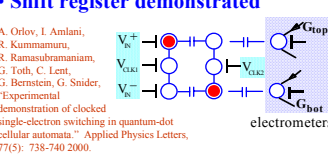
A. Orlov, R. Kumamuru, R. Ramasubramaniam, G. Toth, C. Lent, G. Bernstein, G. Snider, "Experimental demonstration of a latch in Clocked quantum-dot cellular automata: Review and recent Experiments." *J. of Appl. Physics*, 85: 4283-85, 1999.

- Molecular QCA



C. Lent, "Molecular electronics: Bypassing the transistor paradigm." *Science*, 288:1597-1599, 2000.

- Shift register demonstrated



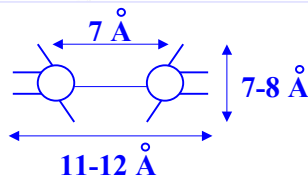
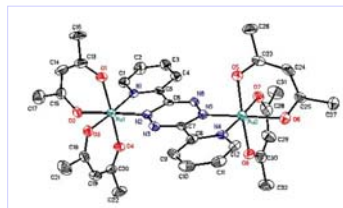
A. Orlov, I. Amlani, R. Kumamuru, R. Ramasubramaniam, G. Toth, C. Lent, G. Bernstein, G. Snider, "Experimental demonstration of clocked single-electron switching in quantum-dot cellular automata." *Applied Physics Letters*, 77(5): 738-740 2000.



2-Dot QCA Molecules

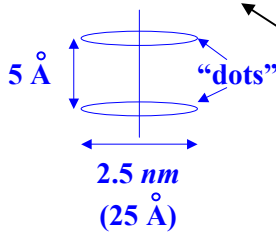
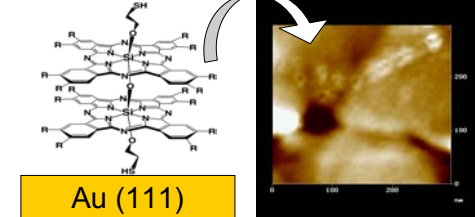
From ND DARPA Moletronics project

Mixed-valance ruthenium dimers



(Center distance of adjacent molecules: ~14 Angstroms)
(M. Lieberman, et al, 2002)

Silicon phthalocyanine dimers

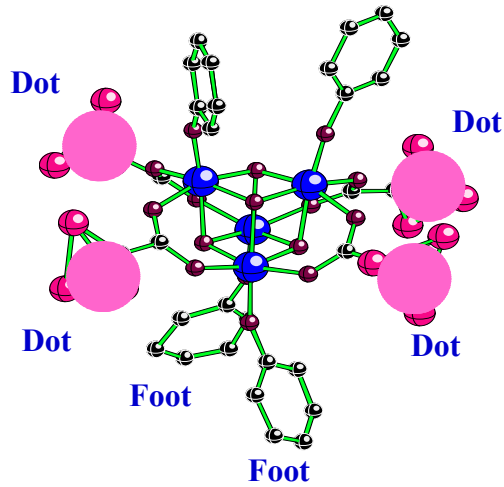


Binds flat on Au surface
Forms self-limiting monolayer
(M. Lieberman)
Appears to self-align
(E. Greenbaum)

These molecules are *real* - in lab now



4 dot Core-cluster molecules



Variants with
"feet" for
surface binding
and orientation

From ND DARPA Moletronics project

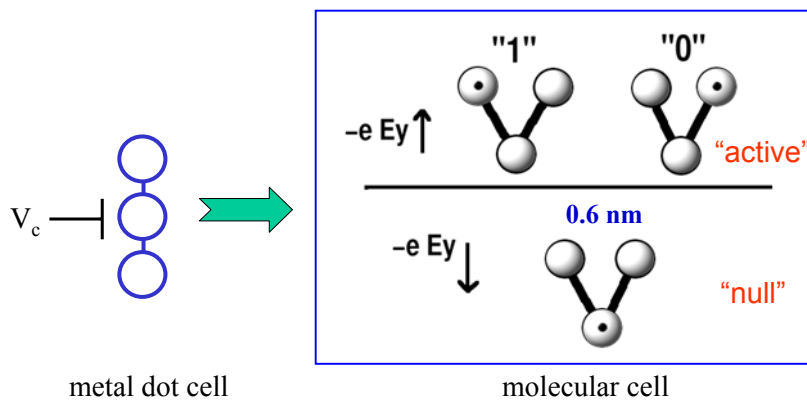
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New Device Focus: 3 dot 3D QCA molecules



Note: "null state" has some valuable circuit properties
- and may allow for "CMOS" static programming

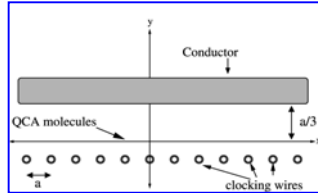
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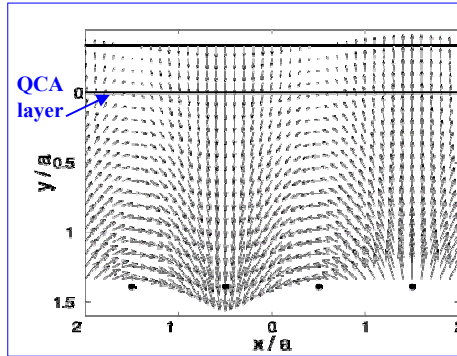
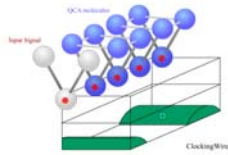
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Mixed Technology Clocking



Hennessey and Lent, *JVST* (2001)

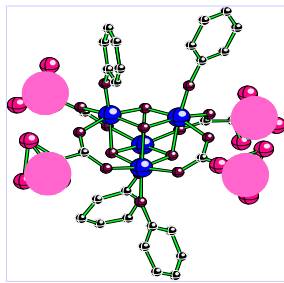


Clocking field is provided by **buried Si wires** (CMOS controlled).
 ITRS 2016 wire pitch: 22 nm ~ 5-10X molecular cell size.



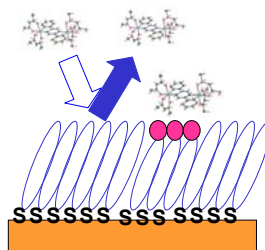
Attachment mechanisms

Core cluster molecules



Variations with "feet" for surface binding and orientation

Surface attachment of ruthenium dimers



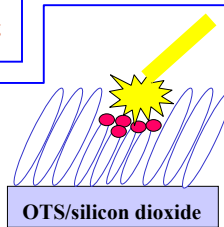
Self-limiting binding to hydrophilic surfaces

No binding to hydrophobic surfaces

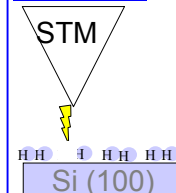
(M. Lieberman, G. Bernstein)

Electron-beam lithography

(OTS: M. Lieberman)
 (E-beam: G. Bernstein)
 (30nm tracks from 5nm primary beam)



Also, STM...

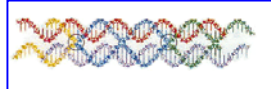




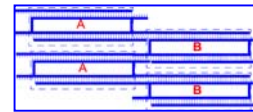
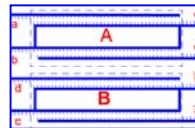
Non-lithographic patterning with DNA tiles

- Double-crosslinked DNA files

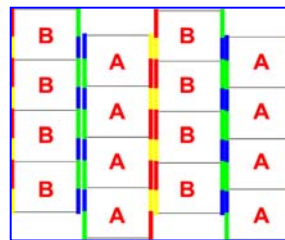
(Winfree, Lu, Wenzler, and Seeman, *Nature* 394, p. 539 (1998))



- Watson-Crick complement



- Wang tiles



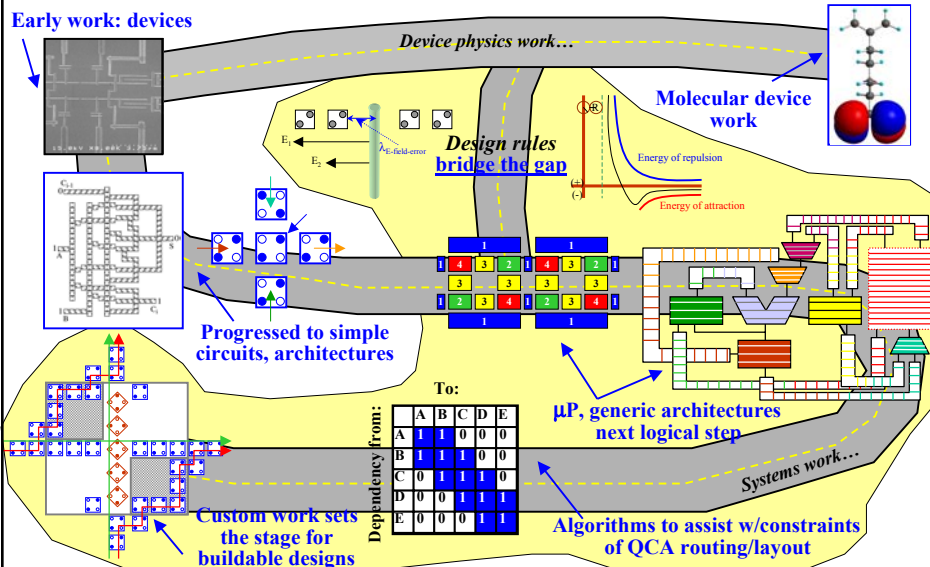
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A “QCA Logic Roadmap”



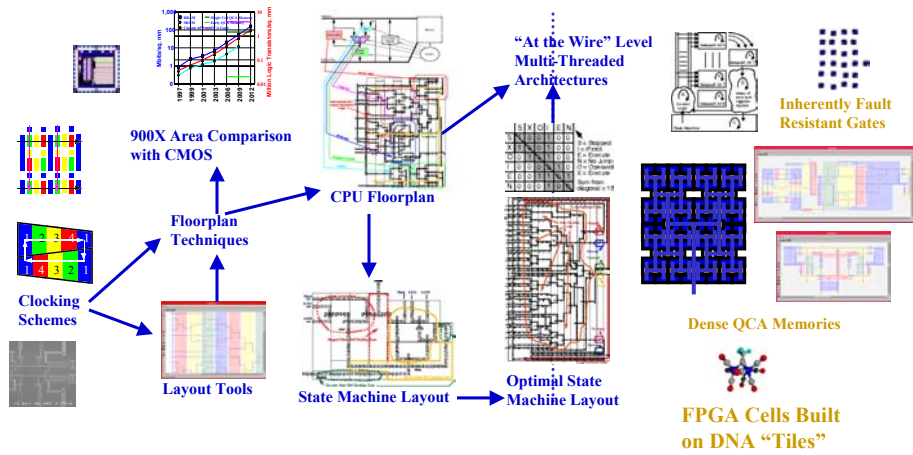
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Designing with QCA



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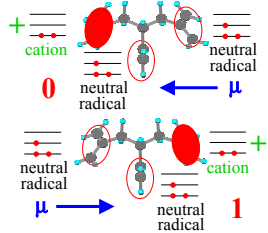
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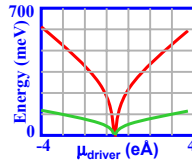


Design rules – placement

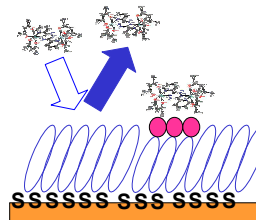
Interaction = computation = 1s & 0s
1s & 0s = dipole moments of molecules



Dipole interaction drops off by factor of d^3
>> potential for "mistake"



Systems perspective: what if cell doesn't attach?



(Courtesy: M. Liebermann)

QCA cells must attach to some substrate (DNA grid possible?)



Will dictate specific attachment points

1st "design rule": interaction, placement of 2 adjacent cells

Many physical problems are solved by adding a clock. But what does "adding a clock" mean from systems perspective?

Interactions...

Charge-charge		1/d
Charge-dipole		1/d ²
Dipole-dipole		1/d ³
Charge-induced dipole		1/d ⁴
Dipole-induced dipole		1/d ⁵
Dispersion		1/d ⁶
van der Waals radius		1/d ¹²

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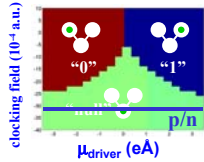
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Design rules – functionality

E-field needs certain **magnitude** to push e^-/h^+ up to **active** site
 Function of molecule, packing distance, etc.

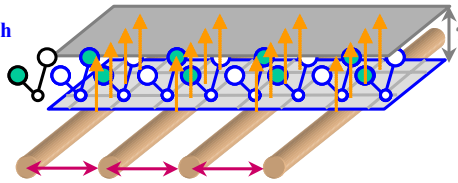
Clock – affects dipole strength needed to switch



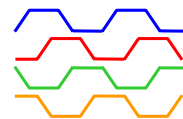
So what about a “clock”?
 • Really an E-field
 • Makes cells **active**...
 • ...or makes cells **null**
 • Can be generated by CMOS wires under attachment substrate

So, what does the clock do for the system designer?

E-field makes cells **active** or **null**
Active cells = computation
 E-field determines **area** of computation



Data moves in phases



$\pi/2$ phase shift on wires

Clock wire **distance** \uparrow = **information density** \downarrow
Functional density still the same

Clock wires have **numbers** associated with them...

Driven by “conventional” lithography



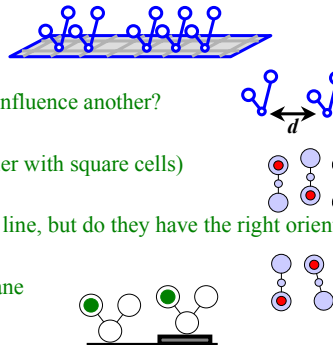
Will also determine clock rate...

- Only interested in E-field’s y-component
- Makes cells **active** or **null**
- Driver controls **1s** or **0s**
- Add a conductor
- Where do we place conductor?



Fault Modeling

- **Background charge**
 - Possible substrates:
 - SiO_2 , organic monolayer on top of SiO_2 DNA tiles
 - All subject to stray charge...
 - Stray charge can excite a cell out of ground state (source of error)
- **Defects**
 - **Error in placing cells**
 - Cells simply may not attach
 - **Distance between cells**
 - At what distance will 1 cell not influence another?
 - **Alignment/Rotation**
 - Cells must “line up to talk” (easier with square cells)
 - **Orientation**
 - Cells may “line up” in a straight line, but do they have the right orientation to talk?
 - **Rough attachment surfaces**
 - cells may not line up in the y-plane



(Conversations with Marya Lieberman)



Summary Comparisons

<u>Base Technology</u>	<u>Silicon</u>	<u>Nano</u>
Component Count	Billions	Uncountable
Fabrication	In layers	Self-Assembly
Memory vs Logic	In same technology	Very technology dependent
Clocking	In same technology	Very technology dependent
Power Distribution	In same technology	Very technology dependent
I/O	In same technology	Very technology dependent
Fault Models	Small	Very visible



Lessons Best Not Forgotten

Or:
We've Been Down This Road
Before!



Some Key Insights from MAW

- **What made the initial technology viable**
- **What allowed follow-on technologies to**
 - Not only survive development
 - But be deployable so quickly
- **The MAW Workshop Experts:**
 - Conway (Michigan): “The Revolution”
 - Abraham (Texas): “Testing & Verification”
 - Irwin (Penn State): “Why the Roadblock”



Conway on Architects

- **Don't care about physics, only rules for composition**
- **Look at designs in layers (hierarchies)**
- **Successful ones work with others: circuit designers, CAD, packaging, layout, fab...**
- **Tend to translate new technologies into different forms of old (abstraction)**



Conway on Technology circa 1977: RTL

- Design flow:
system arch => logic designers => fab
 - With very little interaction
- Devices looked at in cross section, NOT overhead (*“Just like Today!!”*)
- “You just wire’em up”
- MOSFET: “slow & sloppy”

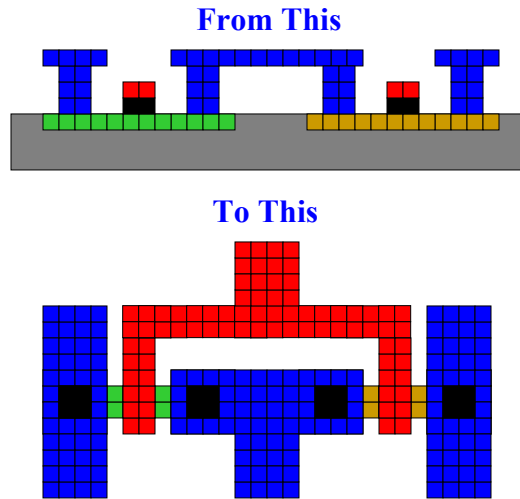


The Mead/Conway Revolution

- Self-aligned gate enables simplified fab
- Realization that scaling to 0.25u was feasible
- Energized academic design community
 - *Scaling rules for technology independent design*
 - *Some simple but useful circuit primitives*
 - *A focus on interconnect, not cross section*
- Early work considered toy-like, unoptimizable
 - *UNTIL MOSIS enabled inexpensive, adventuresome prototyping*



The Mead/Conway Revolution: A Change in Perspective



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The Power of Hierarchies & Abstraction

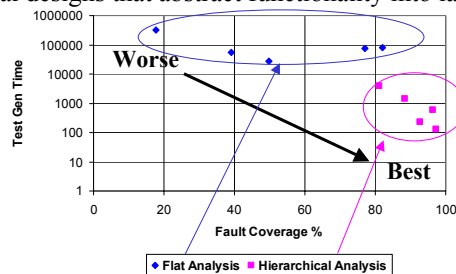
(abstracted from J. Abraham)

Observations:

- 200 bits covers more states than there are protons in universe
- Many key design questions NP-complete: Critical paths, verification, fault coverage, ...

Lesson Learned from CMOS CAD

- Direct attack on “flat designs” rapidly becomes impossible
- Hierarchical designs that abstract functionality into layers are manageable



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What Are *We Now* Good At?

- **The Digital Paradigm: a time-tested model**
 - State machines, data path, memory, busses, ...
- **“Abstracting Out” the physics**
- **Focus on Interconnect, not devices**
- **Hierarchical design from day one**
- **Portable design styles**
- **Working with device & circuit designers to**
 - Invent new structures
 - That permit more efficient designs
- **Automating routine design activities**
- **Fabricating real chips on student schedules**



A Transitional Curriculum

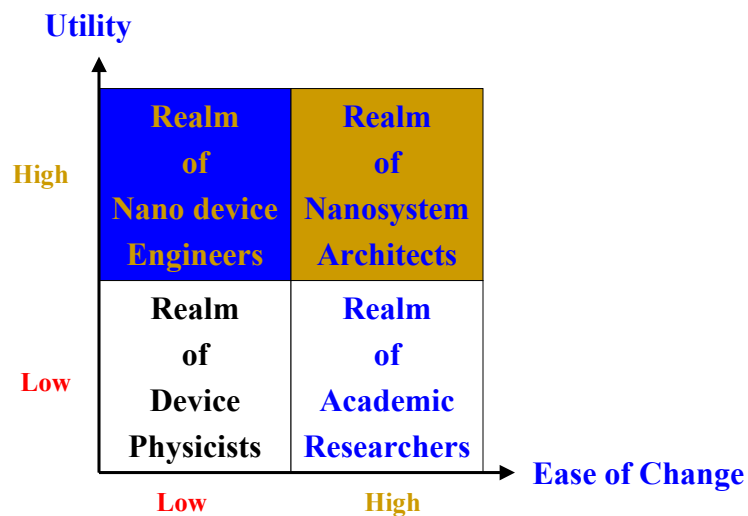


Our Objectives

- Train the next generation
- To design systems
- With billions (“and billions”) of components
- That interface with the real world
- That work
- When we may not understand the technology today



Where Should We Focus





Considerations

<u>Base Technology</u>	<u>Silicon</u>	<u>Nano</u>
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Our Ideal Students: The “Dream Nano Team”

- **Device physicists:**
 - Simplified technology description teachable quickly to “anyone”
 - Description of “Key Parameters” that affect circuit level performance
 - Simple basic circuits
- **Architects:**
 - Develop abstractions for hierarchical designs
- **CAD Engineers:**
 - Leverage existing hierarchical design systems where possible
- **Physical Designers:**
 - Simple interfaces to conventional technology & environment

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What to Keep from Current Curriculum

- **“Logic” as a paradigm**
- **Abstraction**
- **Design Rules**
- **Hierarchies**
- **Layout orientation**
- **Timing**
- **Relationship between microarchitecture, architecture (ISA), languages, support tools**

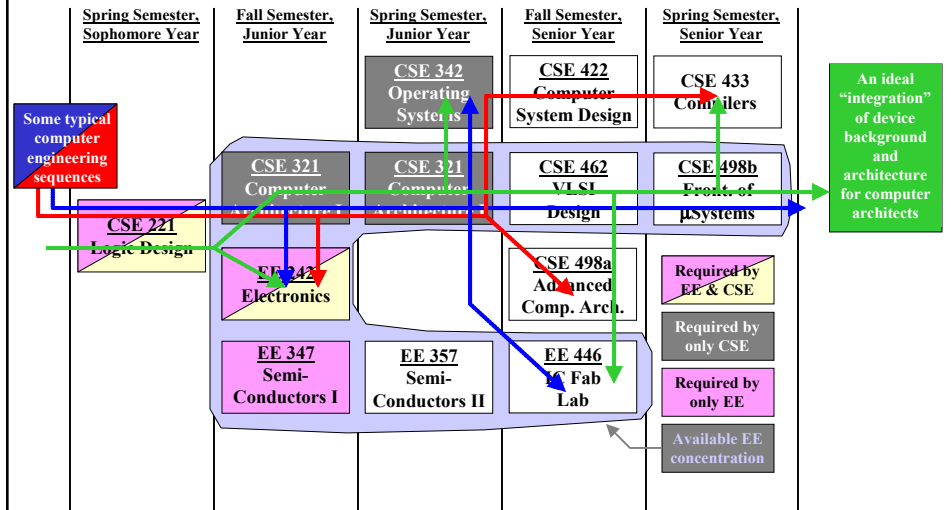


What to Add

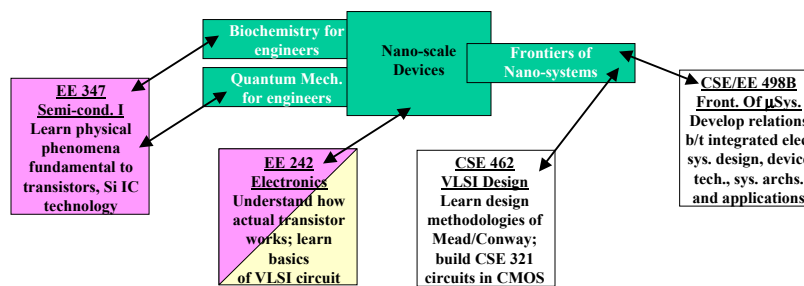
- **Enough physics to justify new, generic “device types”**
- **More emphasis on fault models**
- **Fault redundancy techniques**
- **Mixed technology interfacing**
- **Self-assembly**
- **New computational paradigms**



“You’re friendly, neighborhood school for computer architects”



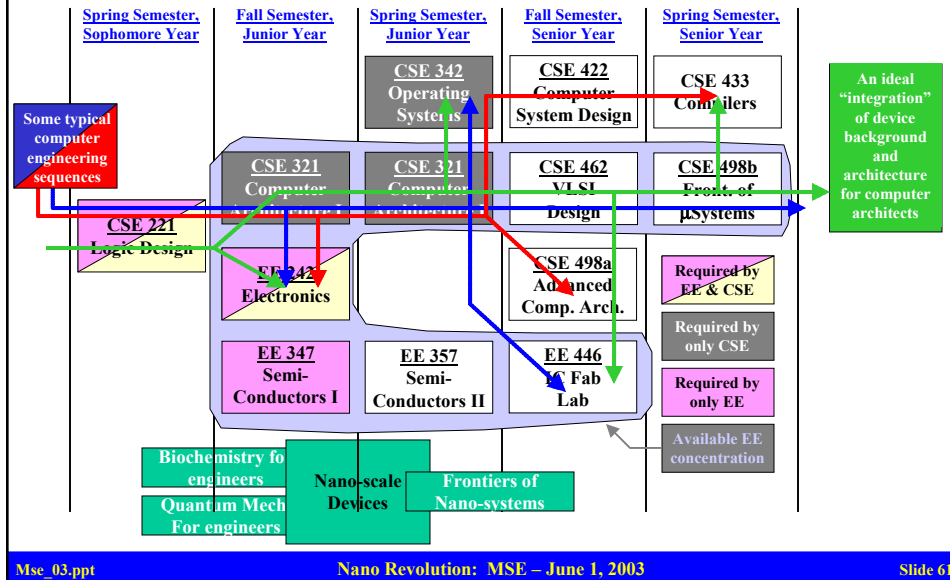
What’s new?



- **Biochemistry/QM for engineers vs Semi-conductors:**
 - All teach about materials computational devices built from
- **Nano-scale devices vs Electronics:**
 - Both teach about how computational devices actually function
- **Frontiers of nano-systems vs VLSI/Frontiers of μ Systems**
 - Currently nano-“capstone” course = combination of MOS capstone course – goal is to help students *evolve*



“You’re friendly, neighborhood school for nano-architects”



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The Technology Package

- **Engineering-oriented ground rules**
 - Projectable into future technology generations
- **Can be taught quickly**
- **Simple models of speed, power, area**
- **Permit hierarchical design**
 - Primitive composition rules
 - Reasonable I/O
 - Leverage test & validation technologies
- **Basic tool sets readily available**
- **Matched with “readily accessible prototyping service”**

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A Desirable Nano Prototyping Facility

- **“Open” to wide group of potential users**
- **Permit Spectrum of Activities**
 - **Student design exercises**
 - **New circuit experiments**
 - **New architectural prototypes**
- **Rapidly reach “Proof of Concept” stage**



Concluding Thoughts



Conclusions

- Our students *will* see nano .. and soon
- We *can* introduce “nano” at the device level today
- We *must* do so in a design friendly way
- We also need to *plan for* new topics:
 - Self assembly, fault tolerance
- Working with the device physicists *will help*
- As will availability of nano lab facilities



Needed Insight

- Understanding & modeling of molecular interactions
 - And abstraction into simple “engineering” models
- What is resulting “electronic nanotechnology”
- “Killer Apps”/new computing models
- Construction of hierarchy of abstractions
 - With “interface” to conventional environments
 - Most reasonable starting point: FPGA-like arrays
- How to provide reliability from the beginning



A Followup Activity

- **“Nano Training Bootcamp”**
 - **Basic theory**
 - **Nano device structure**
 - **Fabrication techniques**
 - **Characterization**
- **Institute for Nanotechnology, Northwestern**
- **July 8-11, Evanston IL**
- **www.asme.org/nano/bootcamp**